WHAT IS CLAIMED IS:

1. A converter comprising a first substrate having a detection face; a movable electrode provided with a space from the detection face of said first substrate and capable of being displaced to and from said first substrate; a fixed electrode provided on the detection face of said first substrate; and a first signal fetching section electrically connected to said movable electrode, wherein said first signal fetching section is formed with metal having high corrosion resistance, and said movable electrode is formed by dry-etching single-crystal silicon with the specific resistance held at 1.0 Ω• cm or below by mixing therein dopant lowering the resistance value.

2. A converter comprising a first substrate having a detection face; a movable electrode provided with a space from the detection face of said first substrate and capable of being displaced to and from said first substrate; a fixed electrode provided on the detection face of said first substrate; and a first signal fetching section electrically connected to said movable electrode, wherein said first signal fetching section is formed with metal having high corrosion resistance, and said movable electrode is formed by wet-etching single-crystal silicon with the specific resistance held in a range from 0.005 to 1.0 Ω• cm or below by mixing therein dopant lowering the resistance value.

3. The converter according to claim 1, wherein the silicon forming said movable electrode has the p-conduction type.

4. The converter according to claim 2, wherein the silicon forming said movable electrode has the p-conduction type.

5. The converter according to claim 1, wherein the metal forming said first signal fetching section is titanium.

6. The converter according to claim 2, wherein the metal forming said first signal fetching section is titanium.

7. The converter according to claim 3, wherein the metal forming said first signal fetching section is titanium.

8. The converter according to claim 4, wherein the metal forming said first signal fetching section is titanium.

9. The converter according to claim 1 further comprising:

a second substrate provided with a space to a surface of said movable electrode in the contrary side from the surface opposing to the detection face of said first substrate, wherein an extended section extending outward more as compared to a side face of said first substrate is provided on said second substrate, and said first signal fetching section is provided spanning from a surface of said extended section in the side closer to said first substrate up to a surface in the contrary side from the detection face of said first substrate.

10. The converter according to claim 2 further comprising a second substrate provided with a space from a surface of said movable electrode in the contrary side from the surface opposing to the detection face of said first substrate, wherein an extended section extending outward more as compared to a side face of said first substrate is provided on said second substrate, and said first signal fetching section is provided spanning from a surface of said extended section in the side closer to said first substrate up to a surface in the contrary side from the detection face of said first substrate.

11. The converter according to claim 9, wherein a wire bonding pad is provided in said first signal fetching section; said wire bonding pad has at least two layers; the lower layer section is formed with metal well adapted to conjunction with an oxide film on a surface of metal forming said first signal fetching section; and the upper layer section is

formed with metal well adapted to conjunction with said lower layer section and having good bondability and high corrosion resistance.

12. The converter according to claim 10, wherein a wire bonding pad is provided in said first signal fetching section; said wire bonding pad has at least two layers; the lower layer section is formed with metal well adapted to conjunction with an oxide film on a surface of metal forming said first signal fetching section; and the upper layer section is formed with metal well adapted to conjunction with said lower layer section and having good bondability and high corrosion resistance.

13. The converter according to claim 1, wherein the converter is an electrostatic capacitance type of pressure sensor chip in which a pressure to be measured is introduced to a first face of said movable electrode opposite to a second face facing the detection face of the first substrate.

14. The converter according to claim 2, wherein the converter is an electrostatic capacitance type of pressure sensor chip in which a pressure to be measured is introduced to a first face of said movable electrode opposite to a second face facing the detection face of the first substrate.

15. A method of manufacturing the converter according to claim 9 comprising the steps of:

establishing anodic bonding between said first and second substrates and the movable electrode; and

forming said first signal fetching section by means of mask evaporation.

16. A method of manufacturing the converter according to claim 10 comprising the steps of:

establishing anodic bonding between said first and second substrates and the

movable electrode; and

forming said first signal fetching section by means of mask evaporation.

17. A method of manufacturing the converter according to claim 11 comprising the steps of:

establishing anodic bonding between said first and second substrates and the movable electrode; and

forming said first signal fetching section by means of mask evaporation.

18. A method of manufacturing the converter according to claim 12 comprising the steps of:

establishing anodic bonding between said first and second substrates and the movable electrode; and

forming said first signal fetching section by means of mask evaporation.

19. A method of manufacturing the converter according to claim 11 comprising the steps of:

establishing anodic bonding between said first and second substrates and the movable electrode;

forming a lower layer section of said wire bonding pad by means of mask evaporation; and

forming an upper layer section of said wire bonding pad in succession without a surface of the lower layer section of the wire bonding pad being oxidized.

20. A method of manufacturing the converter according to claim 12 comprising the steps of:

establishing anodic bonding between said first and second substrates and the movable electrode;

forming a lower layer section of said wire bonding pad by means of mask evaporation; and

forming an upper layer section of said wire bonding pad in succession without a surface of the lower layer section of the wire bonding pad being oxidized.